

SAMSUNG SEMICONDUCTOR INC

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MMBC1623L4**NPN EPITAXIAL SILICON TRANSISTOR**

T-29-19

AMPLIFIER TRANSISTOR**ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	50	V
Collector-Emitter Voltage	V_{CE0}	40	V
Emitter-Base Voltage	V_{EB0}	5.0	V
Collector Current	I_C	100	mA
Collector Dissipation	P_C	350	mW
Storage Temperature	T_{stg}	150	$^\circ\text{C}$

• Refer to MMBC1623L3 for graphs

SOT-23

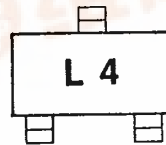


1. Base 2. Emitter 3. Collector

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=40\text{V}, I_E=0$		100	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$		100	nA
DC Current Gain	h_{FE}	$V_{CE}=6\text{V}, I_C=1.0\text{mA}$	90	180	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		1.0	V
Base-Emitter On Voltage	$V_{BE(on)}$	$I_C=1.0\text{mA}, V_{CE}=6\text{V}$	0.6	0.7	V
Current Gain-Bandwidth Product	f_T	$V_{CE}=6\text{V}, I_E=10\text{mA}$ $f=100\text{MHz}$	200		MHz

Marking



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